Ordering number: EN2557B

NPN Epitaxial Planar Silicon Transistor



2SC4188

# Ultrahigh-Definition CRT Display Video Output Applications

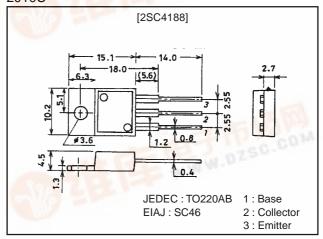
#### **Features**

- · High breakdown voltage :  $V_{CEO} \ge 200V$ .
- Small reverse transfer capacitance and excellent high frequency characteristic: C<sub>re</sub>=1.3pF typ.
- · Adoption of FBET process.

## **Package Dimensions**

unit:mm

2010C



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		200	V
Collecor-to-Emitter Voltage	VCEO		200	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		5	V
Collector Current	l <sub>C</sub>		100	mA
Collector Current (Pulse)	I <sub>CP</sub>		200	mA
Collector Dissipation	PC		1.5	W
		Tc=25°C	10	W
Junction Tempreature	Tj		150	°C
Storage temperature	Tstg	ALC: N	-55 to +150	°C

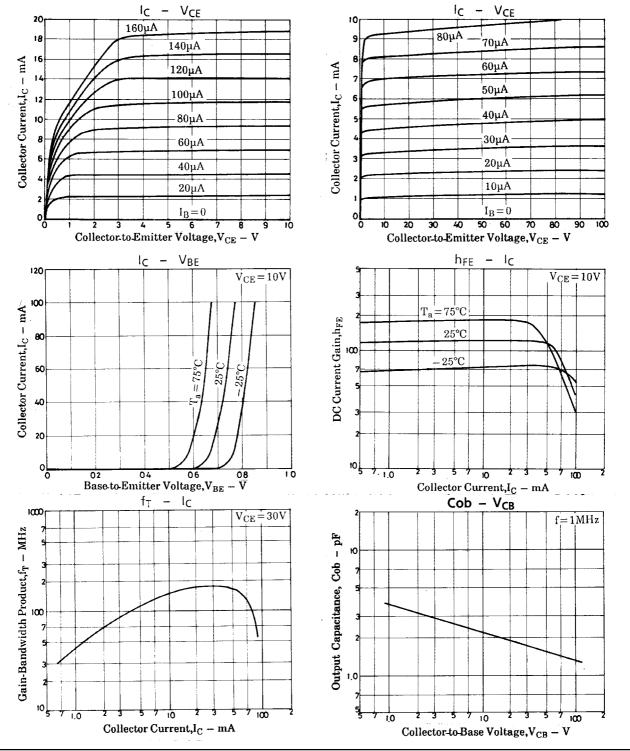
The 2SC4188 is classified by 10mA h<sub>FE</sub> as follows:

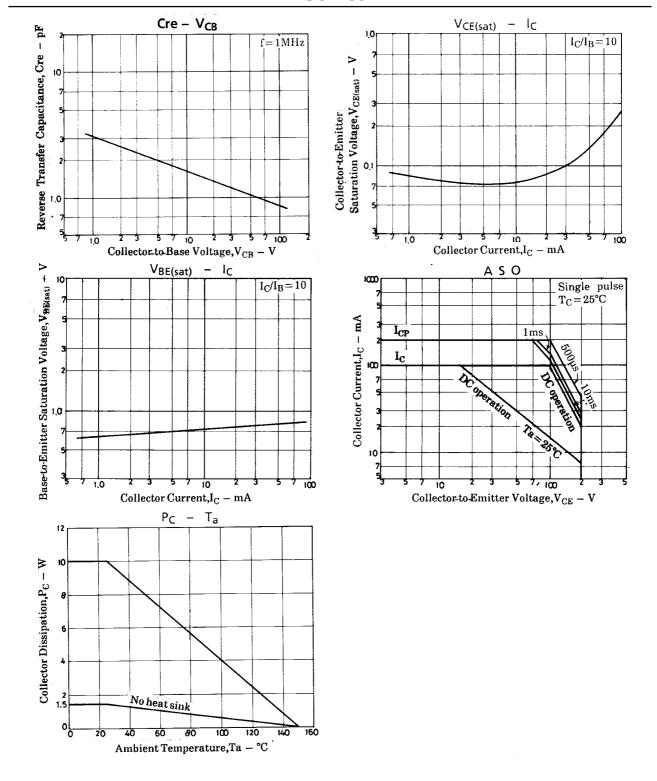
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## Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	UIII
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =150V, I <sub>E</sub> =0			0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	40*		320*	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =30V, I <sub>C</sub> =10mA		150		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =30V, f=1MHz		1.8		pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =30V, f=1MHz		1.3		pF
Collector-to-Emitter Saturatin Voltage	VCE(sat)	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			0.6	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			1.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	200			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	200			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V





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